

ABSTRACT OF THE DISCLOSURE

To provide a manufacturing method for a bipolar gate CMOS semiconductor device, which enables cost reduction and stable element characteristics. In a manufacturing method for a bipolar gate CMOS semiconductor device, an N-type region is selectively formed in a polycrystalline silicon constituting a gate electrode through predeposition using as a mask an insulating film, after which the insulating film is removed to implant P-type impurity ions into an entire surface, whereby the semiconductor device can be provided at a low cost with the stable element characteristics.